

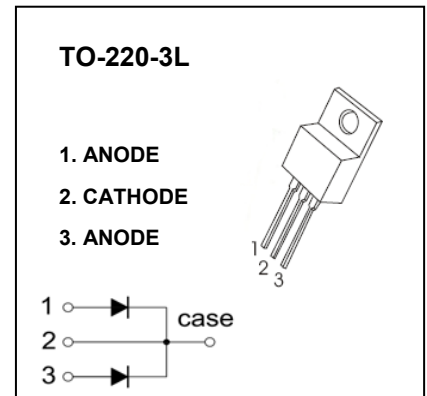


TO-220-3L Plastic-Encapsulate Diodes

MBR20125CT SCHOTTKY BARRIER RECTIFIER

FEATURES

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{RRM}	Peak repetitive reverse voltage	125	V
V_{RWM}	Working peak reverse voltage		
V_R	DC blocking voltage		
$V_{R(RMS)}$	RMS reverse voltage	87.5	V
I_o	Average rectified output current @ $T_c=125^\circ\text{C}$	20	A
I_{FSM}	Non-Repetitive peak forward surge current 8.3ms half sine wave	120	A
P_D	Power dissipation	2	W
$R_{\theta JA}$	Thermal resistance from junction to ambient	50	$^\circ\text{C/W}$
T_j	Junction temperature	125	$^\circ\text{C}$
T_{stg}	Storage temperature	-55~+150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	125			V
Reverse current	I_R	$V_R=125\text{V}$			9	μA
Forward voltage	V_F	$I_F=10\text{A}$			0.87	V